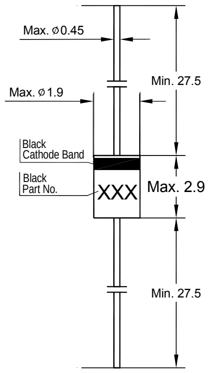
SB721Q-40

Silicon Epitaxial Planar Schottky Barrier Diode

Applications

- High speed switching



Glass Case DO-34
Dimensions in mm

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	40	V
Reverse Voltage	V_R	40	V
Mean Rectifying Current	I_O	30	mA
Peak Forward Surge Current	I_{FSM}	200	mA
Junction Temperature	T_J	125	°C
Storage Temperature Range	T_{stg}	- 40 to + 125	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Min.	Typ.	Max.	Unit
Forward Voltage at I_F = 1 mA	V_F	-	-	0.37	V
Reverse Current at V_R = 25 V	I_R	-	-	0.5	µA
Reverse Voltage at I_R = 10 µA	V_R	40	-	-	V
Capacitance between Terminals at V_R = 1 V, f = 1 MHz	C_T	-	2	-	pF

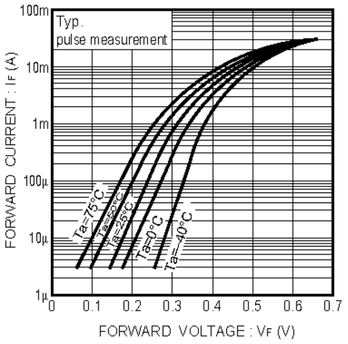


Fig.1 Forward characteristics

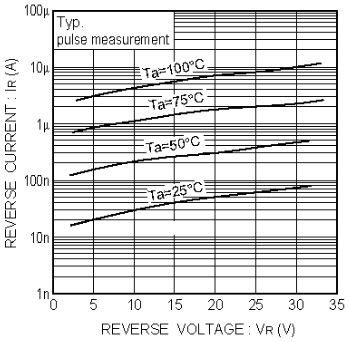


Fig.2 Reverse characteristics

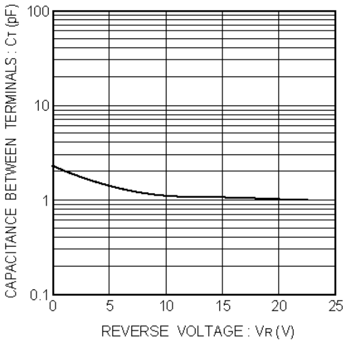


Fig.3 Capacitance between
terminals characteristics

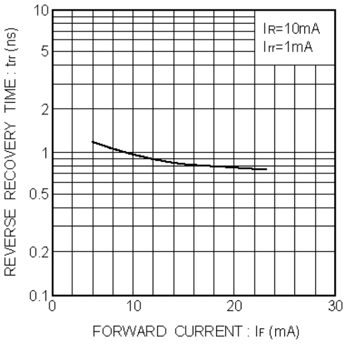


Fig.4 Reverse recovery time
characteristics

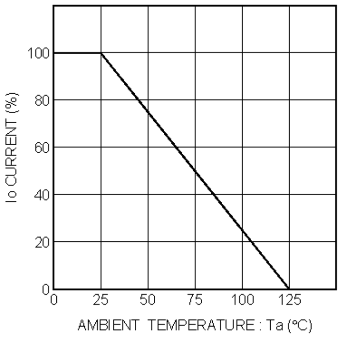


Fig.5 Derating curve
(mounting on glass epoxy PCBs)